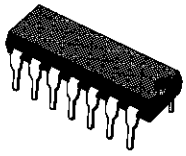
SGS-THOMSON MICROELECTRONICS

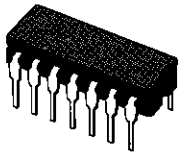
HCC4007UB
HCF4007UB

DUAL COMPLEMENTARY PAIR PLUS INVERTER

- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- MEDIUM SPEED OPERATION t_{PHL}, t_{PLH} = 30ns (typ.) AT 10V
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



EY
(Plastic Package)



F
(Ceramic Package)



M1
(Micro Package)

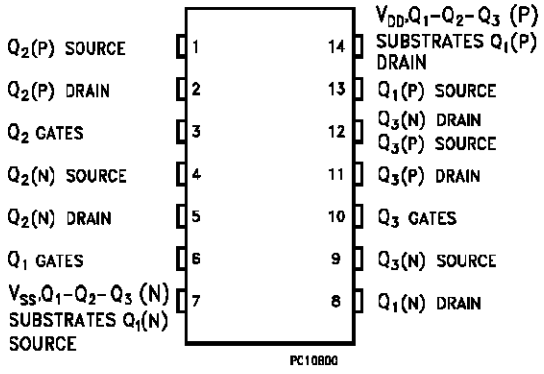


C1
(Chip Carrier)

ORDER CODES :

HCC4007UBF	HCF4007UBM1
HCF4007UBEY	HCF4007UBC1

PIN CONNECTIONS

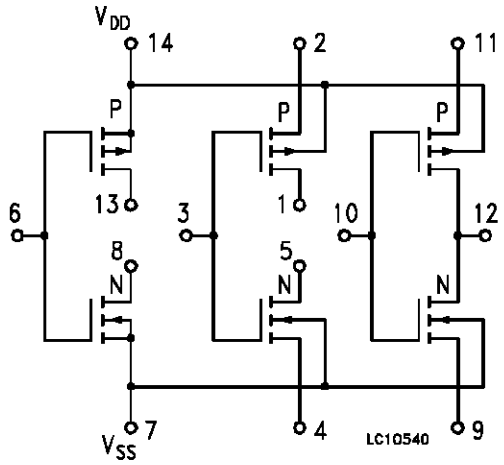


DESCRIPTION

The HCC4007UB is a monolithic integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

The HCC4007UB type is comprised of three n-channel and three p-channel enhancement type MOS transistors. The transistor elements are accessible through the package terminals to provide a convenient means for constructing the various typical circuits as shown in typical applications. More complex functions are possible using multiple packages. Numbers shown in parentheses indicate terminals that are connected together to form the varius configurations listed.

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V_{DD} *	Supply Voltage: **HCC** Types **HCF** Types	-0.5 to +20 -0.5 to +18	V V
V_i	Input Voltage	-0.5 to V_{DD} + 0.5	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package Temperature Range	200 100	mW mW
T_{op}	Operating Temperature: **HCC** Types **HCF** Types	-55 to +125 -40 to +85	^oC ^oC
T_{stg}	Storage Temperature	-65 to +150	^oC

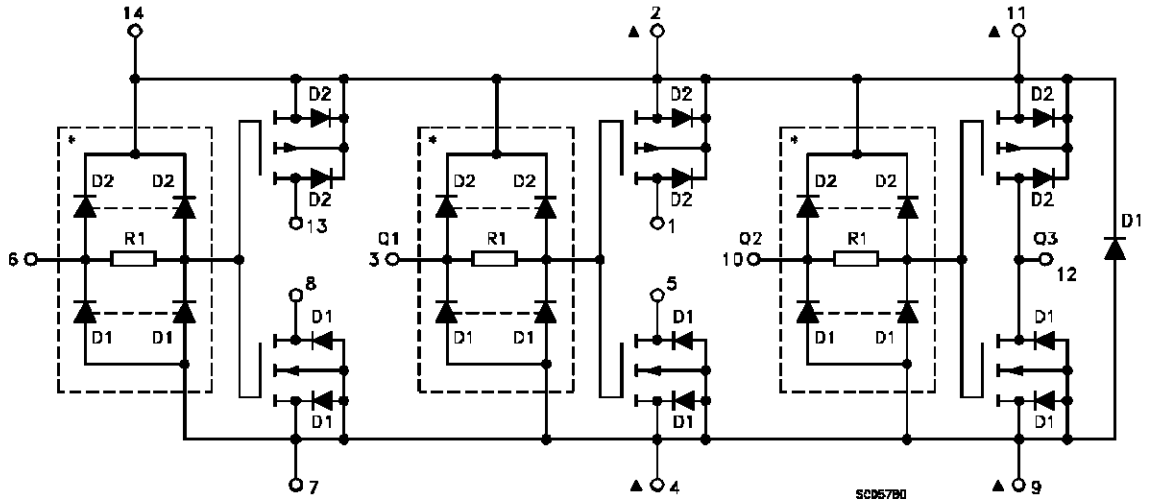
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

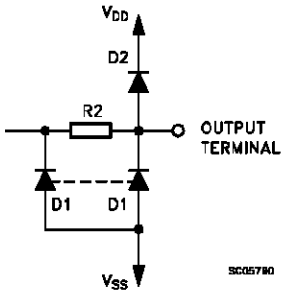
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage: **HCC** Types **HCF** Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature: **HCC** Types **HCF** Types	-55 to +125 -40 to +85	^oC ^oC

SCHEMATIC DIAGRAM (showing input, output and parasitic diodes)





▲ COS/MOS OUTPUT PROTECTION NETWORK BETWEEN TERMINAL NOS. 1, 2, 4, 5, 8, 9, 11, 12, 13, AND THE CORRESPONDING DRAINS AND/OR SOURCES

✳ COS/MOS INPUT PROTECTION NETWORK

PARASITIC AND NETWORK COMPONENTS
D1 = N+ TO P WELL
D2 = P+ TO SUBSTRATE
R1 = 1 - 5 KΩ
R2 = 15 - 30 Ω

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditios				Value							Unit
			V_I (V)	V_O (V)	$\|I_O\|$ (µA)	V_{DD} (V)	T_{LOW} * Min.	T_{LOW} * Max.	25 °C Min.	25 °C Typ.	25 °C Max.	T_{HIGH} * Min.	T_{HIGH} * Max.	
I_L	Quiescent Current	HCC Types	0/5			5		0.25		0.01	0.25		7.5	µA
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
		HCF Types	0/5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
			0/15			15		4		0.01	4		30	
V_{OH}	Output High Voltage		0/5		< 1	5	4.95		4.95			4.95		V
			0/10		< 1	10	9.95		9.95			9.95		
			0/15		< 1	15	14.95		14.95			14.95		
V_{OL}	Output Low Voltage		5/0		< 1	5		0.05			0.05		0.05	V
			10/0		< 1	10		0.05			0.05		0.05	
			15/0		< 1	15		0.05			0.05		0.05	
V_{IH}	Input High Voltage			0.5/4.5	< 1	5	4		4			4		V
				1/9	< 1	10	8		8			8		
				1.5/13.5	< 1	15	12.5		12.5			12.5		
V_{IL}	Input Low Voltage			4.5/0.5	< 1	5		1			1		1	V
				9/1	< 1	10		2			2		2	
				13.5/1.5	< 1	15		2.5			2.5		2.5	
I_{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15		mA
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
			0/15	13.5		15	-3.6		-3.0	-6.8		-2.4		
I_{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36		mA
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I_{IH}, I_{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		±0.1		$±10^{-5}$	±0.1		±1	µA
		HCF Types	0/15			15		±0.3		$±10^{-5}$	±0.3		±1	
C_I	Input Capacitance			Any Input						5	7.5			pF

* T_{LOW} = -55 °C for **HCC** device: -40 °C for **HCF** device.

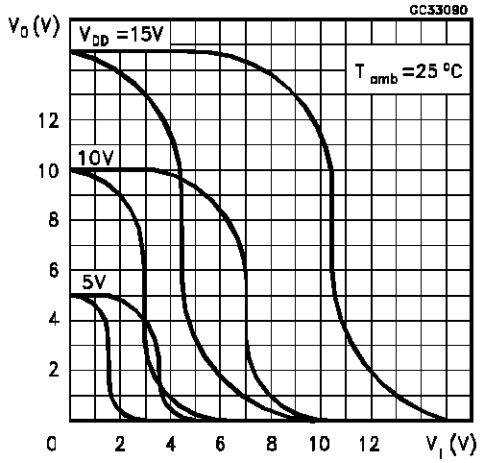
* T_{HIGH} = +125 °C for **HCC** device: +85 °C for **HCF** device.

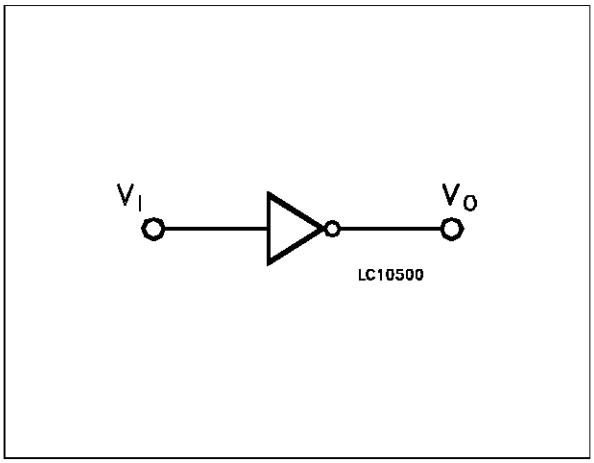
The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25 °C, C_L = 50 pF, R_L = 200 KΩ, typical temperature coefficent for all V_{DD} values is 03 %/°C, all input rise and fall times= 20 ns)

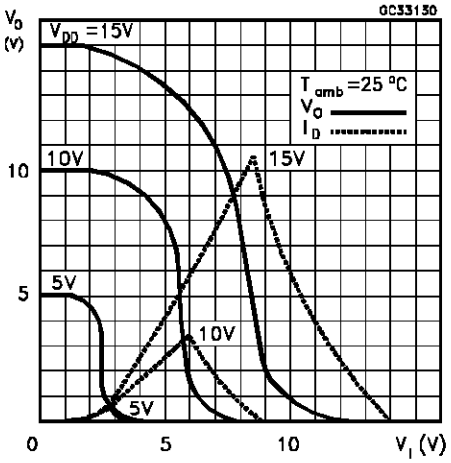
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time		5		55	110	ns
			10		30	60	
			15		25	50	
t_{TLH} t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

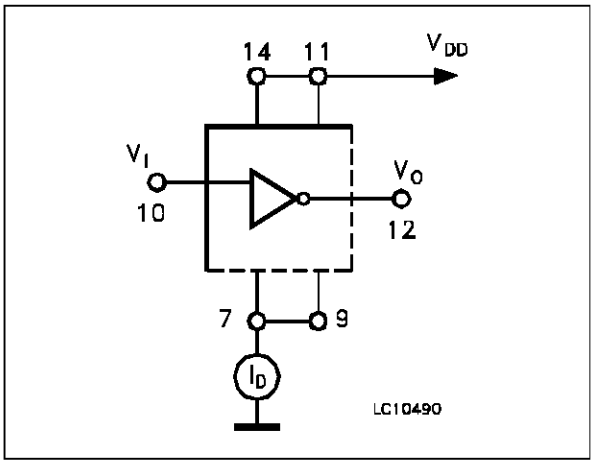
Minimum and Maximum Voltage Transfer Characterisctics for Inverter and test Circuit



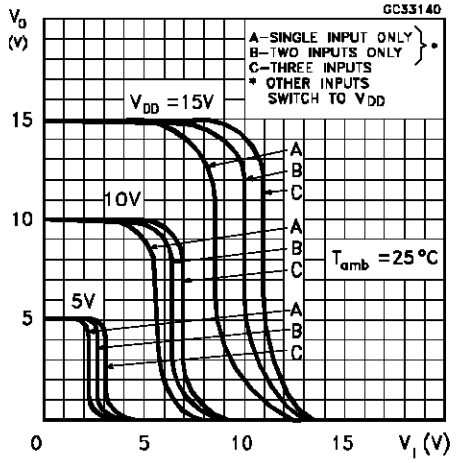


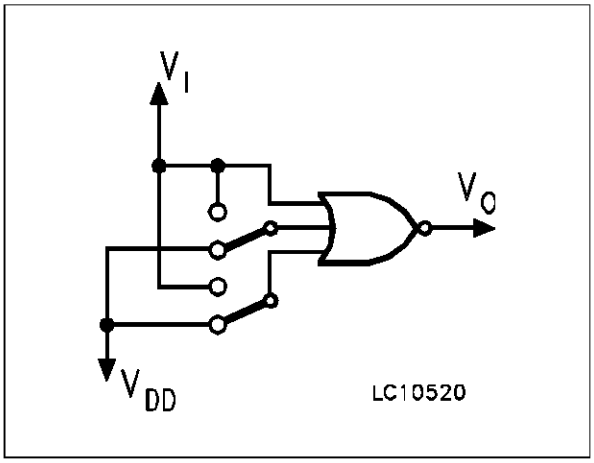
Typical Current and Voltage Transfer Characteristics for Inverter and Test Circuit



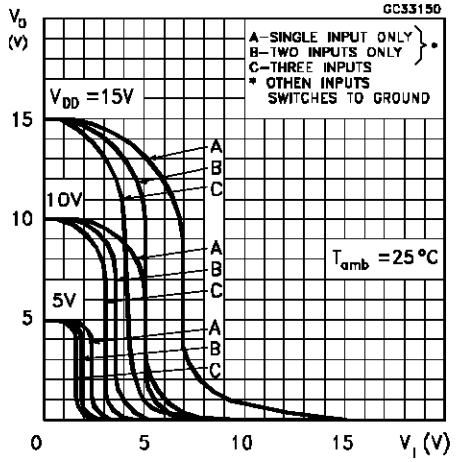


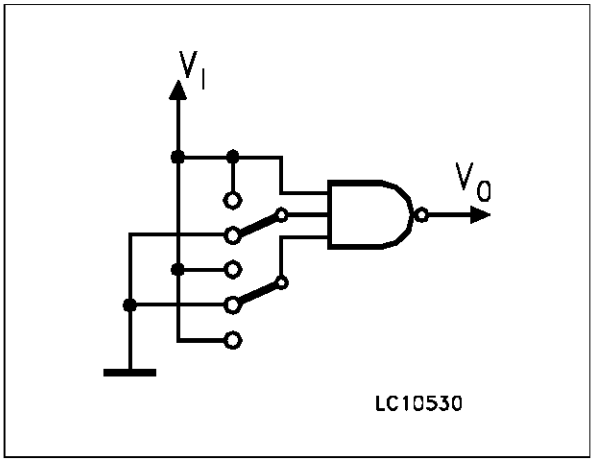
Typical Voltage Transfer Characteristics for NAND Gate and Test Circuit



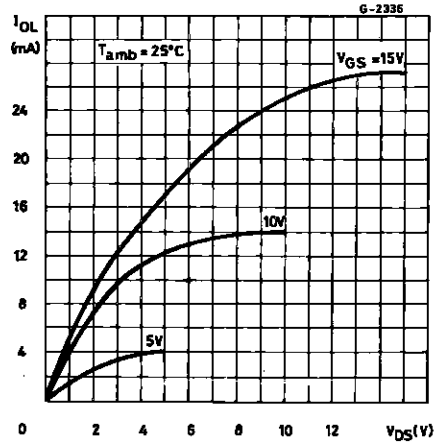


Typical Voltage Transfer Characteristics for NOR Gate and Test Circuit

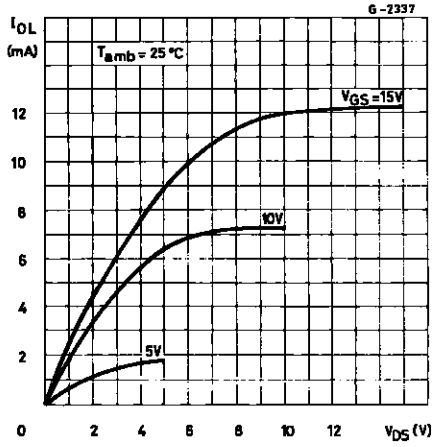




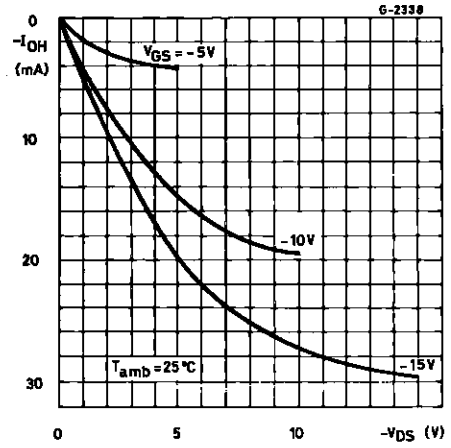
Typical Output Low (Sink) Current Caracteristics



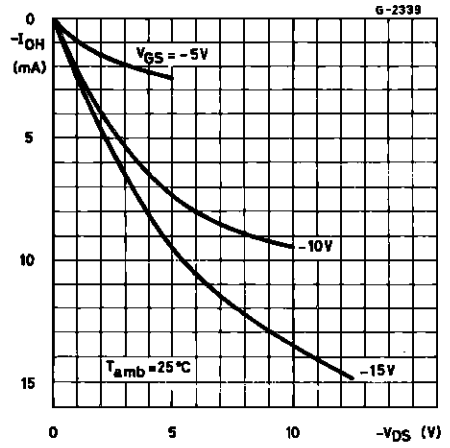
Minimum Output Low (Sink) Current Characteristics



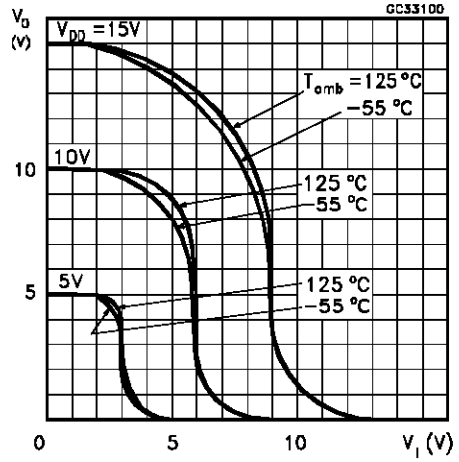
Typical Output High (Source) Current Characteristics



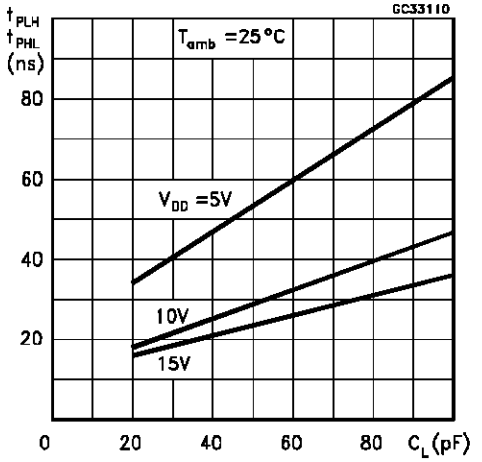
Minimum Output High (Sourrce) Current Characteristics



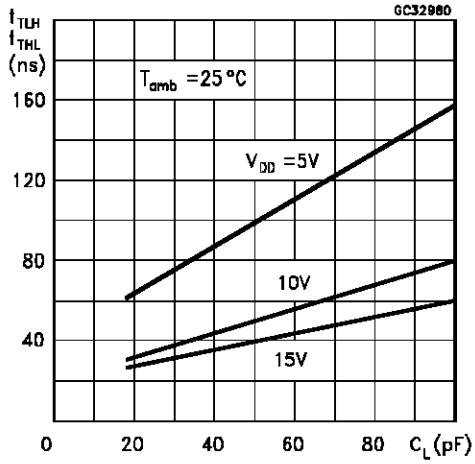
Typical Voltage Transfer Characteristics as a Function of Temperature



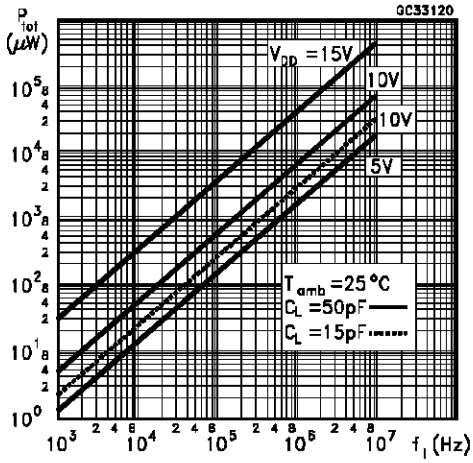
Typical Propagation Delay Time vs. Load Capacitance



Typical Transition Time vs. Load Capacitance

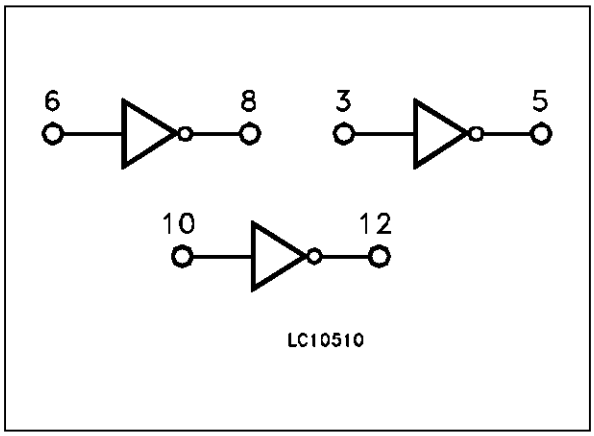


Typical Dissipatio Per Gate vs. Frequency Characteristics

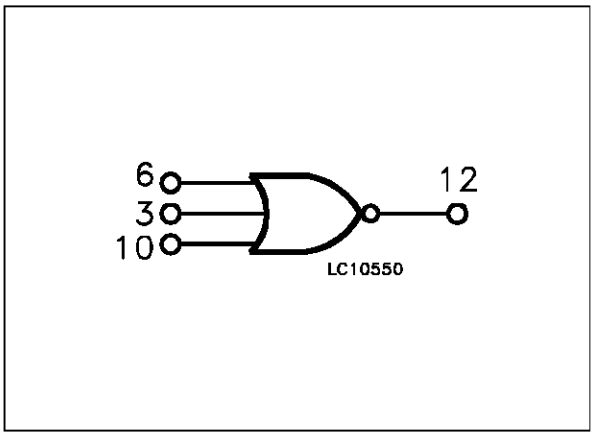


TYPICAL APPLICATIONS (Sample COS/MOS logic circuit arrangements using type 4007UB)

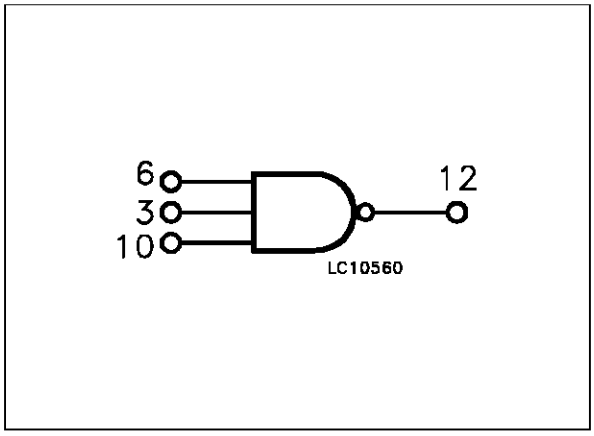
Triple Inverters: (14, 2, 11); (8, 13); (1, 5); (4, 7, 9).



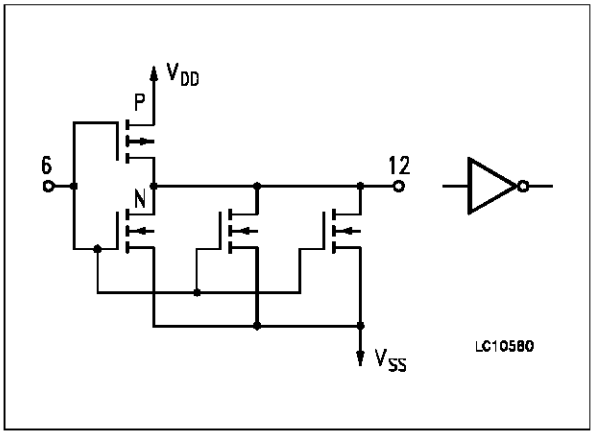
3-Input NOR Gate: (13, 2); (1, 11); (12, 5, 8); (4, 7, 9).



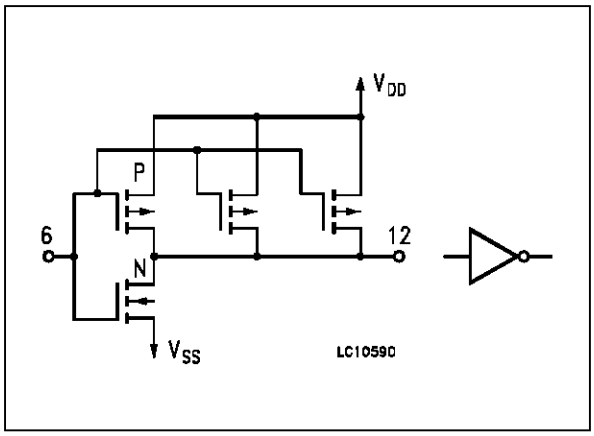
3-Input NAND Gate: (1, 12, 13); (2, 14, 11); (4, 8); (5, 9).



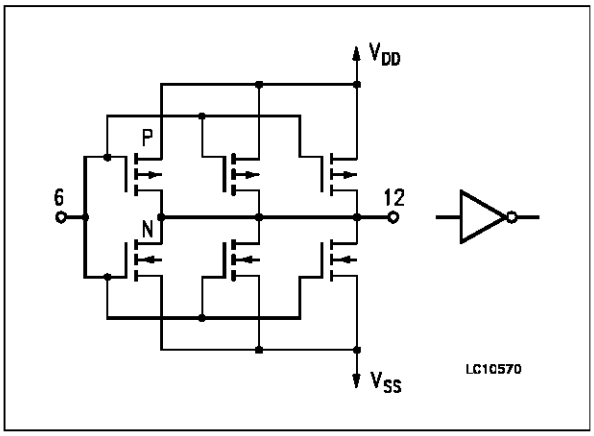
High Sink Current Driver: (6, 3, 10); (8, 5, 12); (11, 14); (4, 7, 9).



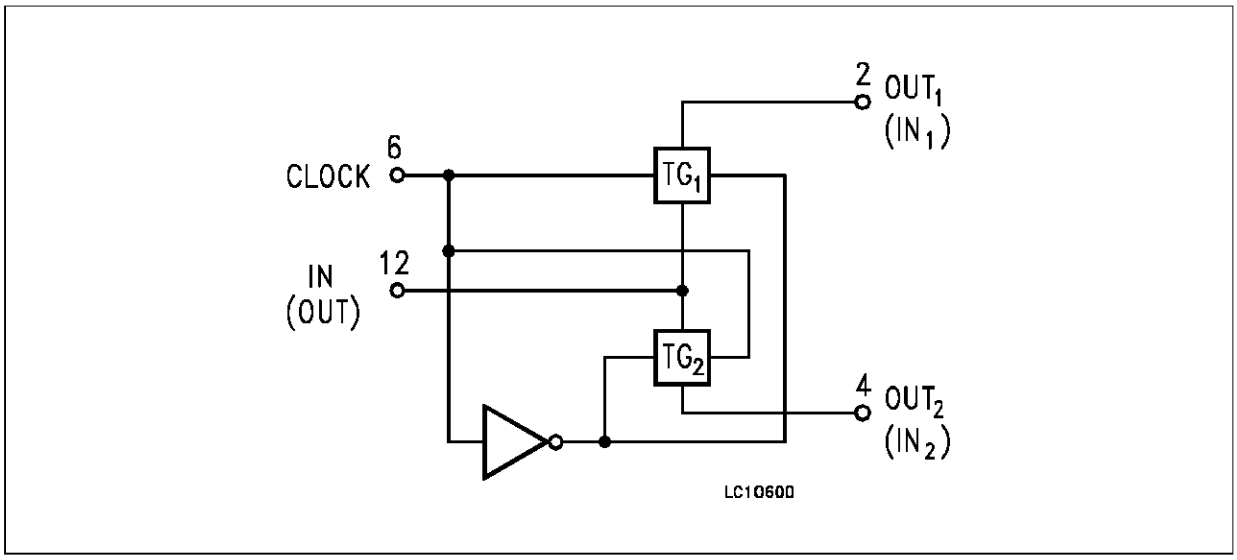
High Source Current Driver: (6, 3, 10); (13, 1, 12); (14, 2, 11); (7, 9).



High Sink and Source Current Driver: (6, 3, 10); (14, 2, 11); (7, 4, 9); (13, 8, 1, 5, 12).

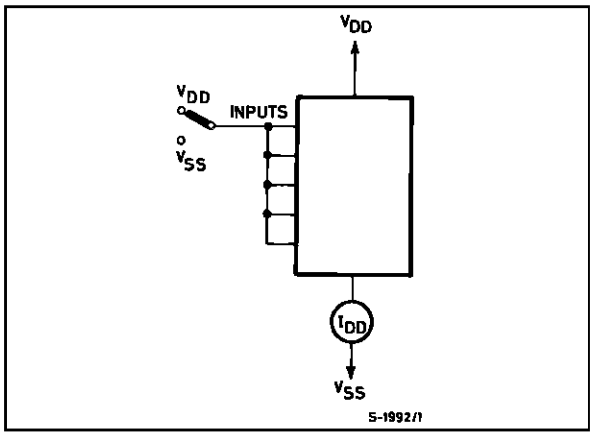


Dual Bidirectional Trasmission Gating: (1, 5, 12); (2, 9); (11, 4); (8, 13, 10); (6, 3).

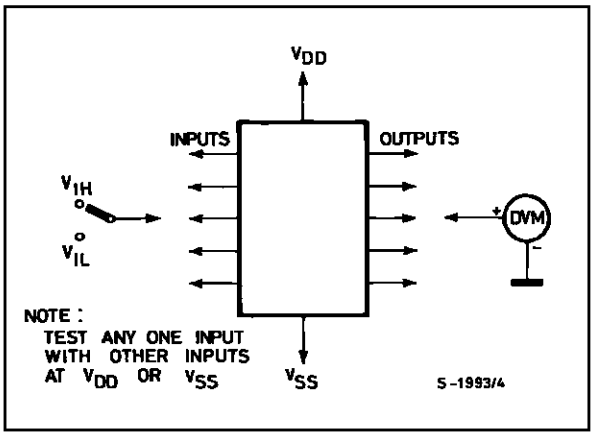


TEST CIRCUIT

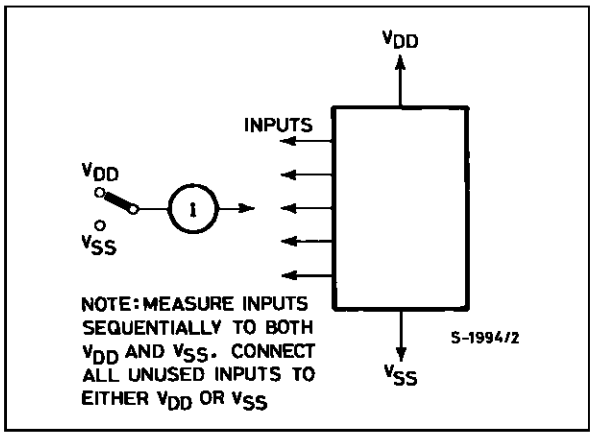
Quiescent Device Current.



Input Voltage.

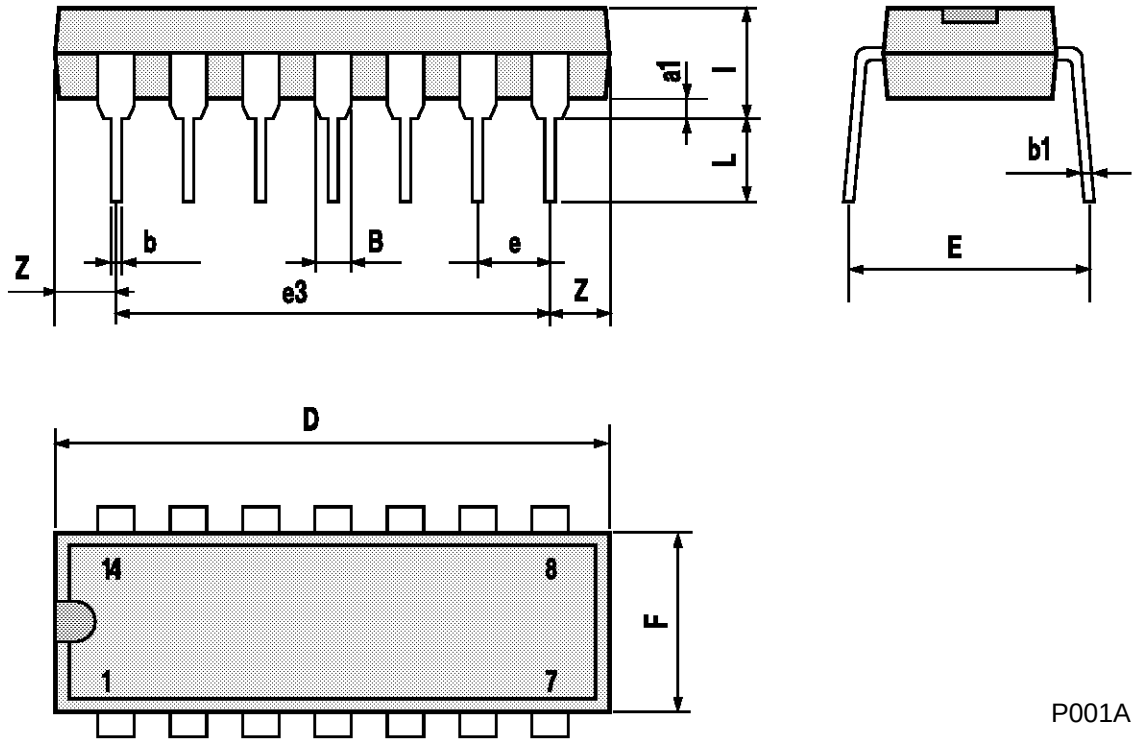


Input Leakage Current.



Plastic DIP14 MECHANICAL DATA

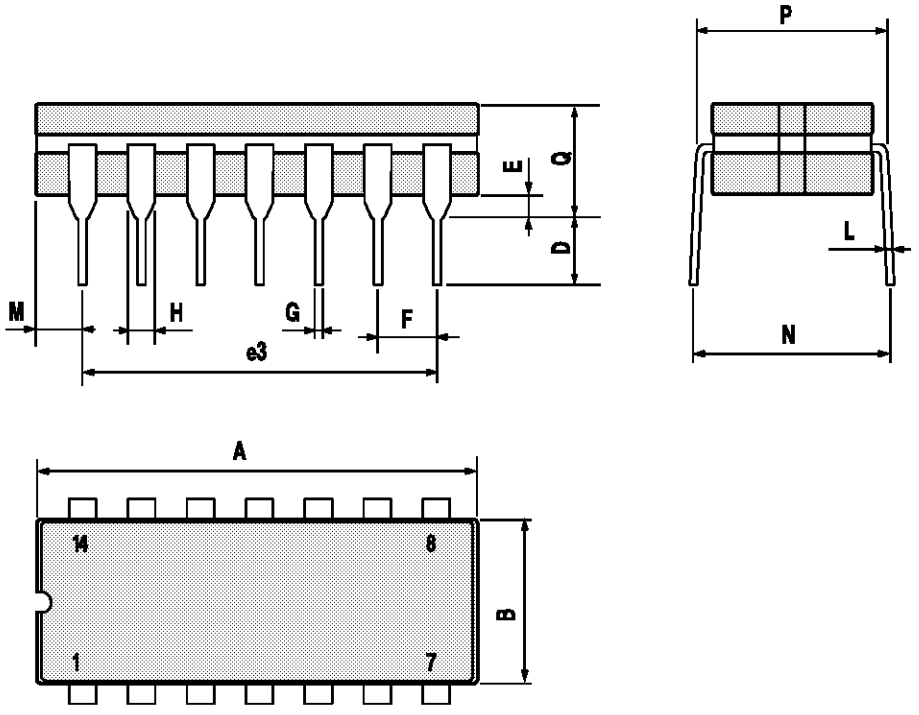
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

Ceramic DIP14/1 MECHANICAL DATA

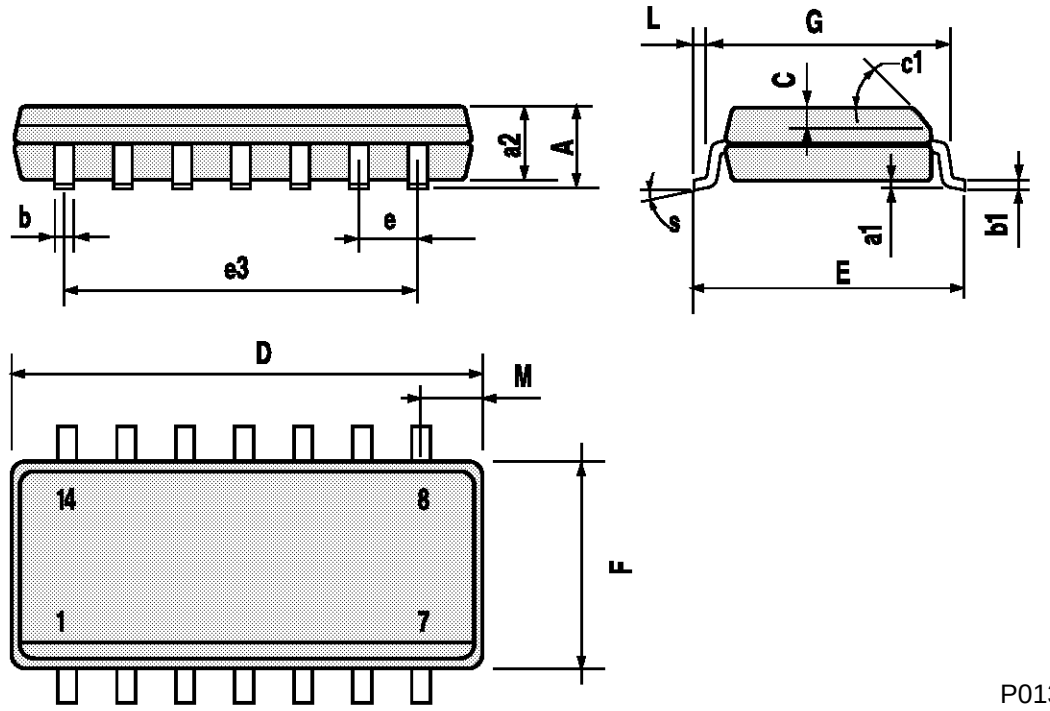
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053C

SO14 MECHANICAL DATA

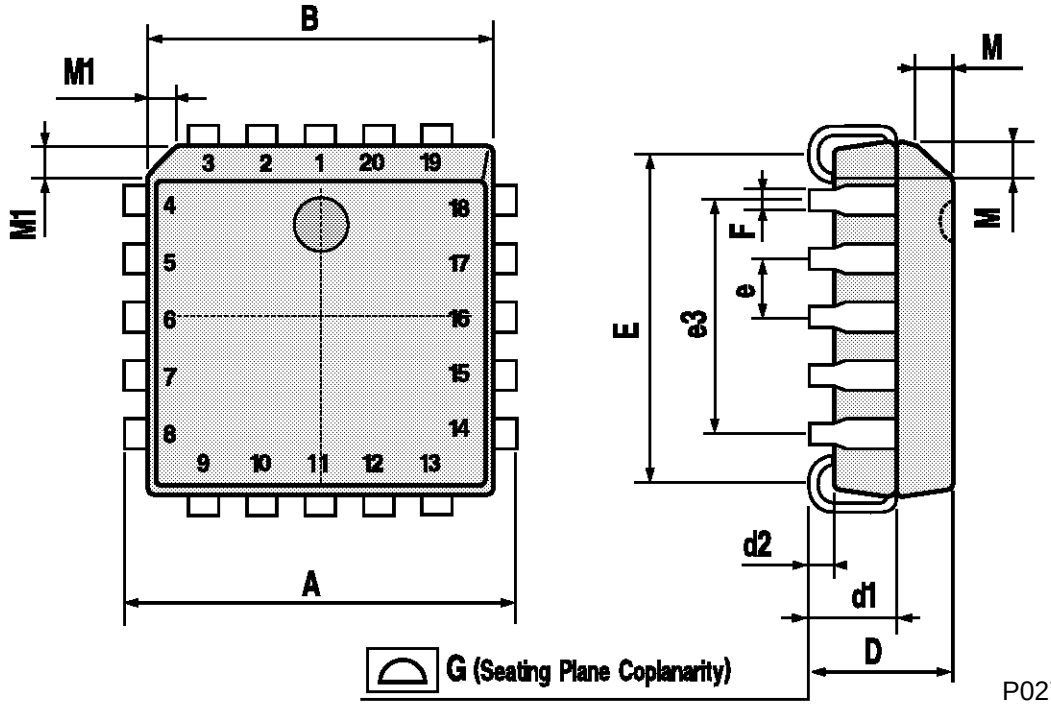
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



P013G

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



P027A

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